

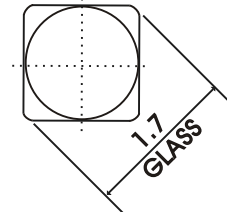
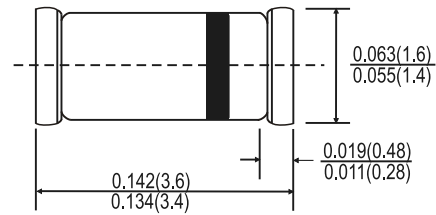
LS4148

SMALL SIGNAL SWITCHING DIODES

FEATURES:

- Silicon epitaxial planar diode
- Fast switching diodes in case QUADRO MELF, especially suited for automatic insertion

QUADRO MELF



Dimensions in inches and (millimeters)

MECHANICAL DATA

Case: QUADRO MELF glass case
Weight: Approx. 0.05gram

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25° C ambient temp. unless otherwise specified.

Single phase, half sine wave, 60 Hz, resistive or inductive load.

For capacitive load, derate current by 20 %.

Characteristic	Symbol	LS4148	Units
Maximum peak reverse voltage	V _{RRM}	100	Volts
Maximum reverse voltage	V _R	75	Volts
Average rectified current .half wave rectification with Resistive load at T _a =25° C And F ≥ 50HZ	I _(AV)	0.15 ¹⁾	Amps
Peak forward surge current, <1S single half sine-wave superimposed on rated load T _a =25° C	I _{FSM}	0.5	Amps
Power dissipation at T _a =25° C	P _{tot}	500 ¹⁾	mW
Maximum instantaneous forward voltage drop per leg at 0.01A	V _F	1.0	Volts
Maximum Voltage rise when switching ON tested with 50mA pulse t=0.1, S, Rise time <30, S, f=5 to 100 KHZ	V _{fr}	2.5	Volts
Maximum leakage current At V _R = 20V At V _R = 75V At V _R = 20V T _a = 150° C	I _R	25 5 50	nA uA uA
Maximum Reverse recovery time	TRR	4	ns
Maximum Junction capacitance V _R = V _F = 0V	C _J	4	PF
Maximum Thermal resistance junction to ambient	R _{th JA}	350 ¹⁾	K / W
MINIMUM rectification efficiency at f = 100MHZ, V _{RF} = 2V	η	045	
Operating temperature range	T _J	-55 to +150	°C
storage temperature range	T _{stg}	-55 to +150	°C

NOTES:

(1) Reverse recovery condition I_F = 0.01A, I_R = 0.001A, V_R = 6V, R_L = 100

1): Valid provided that leads at a distance of 8mm from case are kept at ambient temperature (DO-35)

FIG 1-FORWARD CHARACTERISTICS

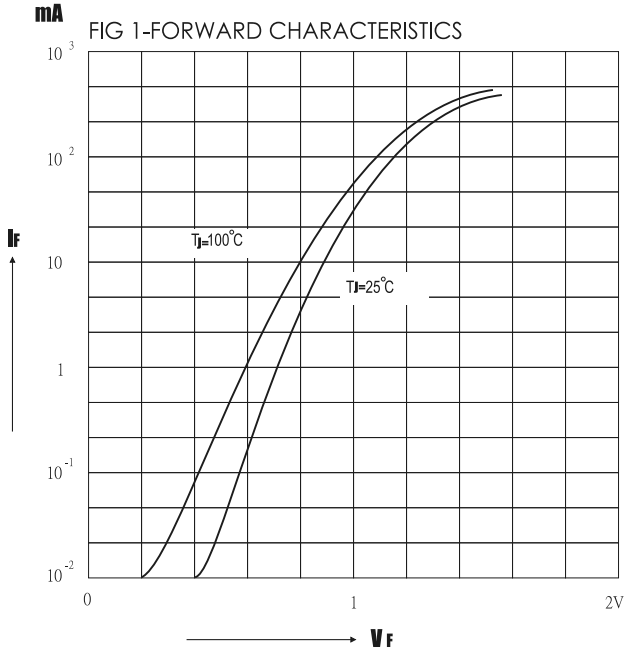


FIG 2: DYNAMIC FORWARD RESISTANCE VERSUS FORWARD CURRENT

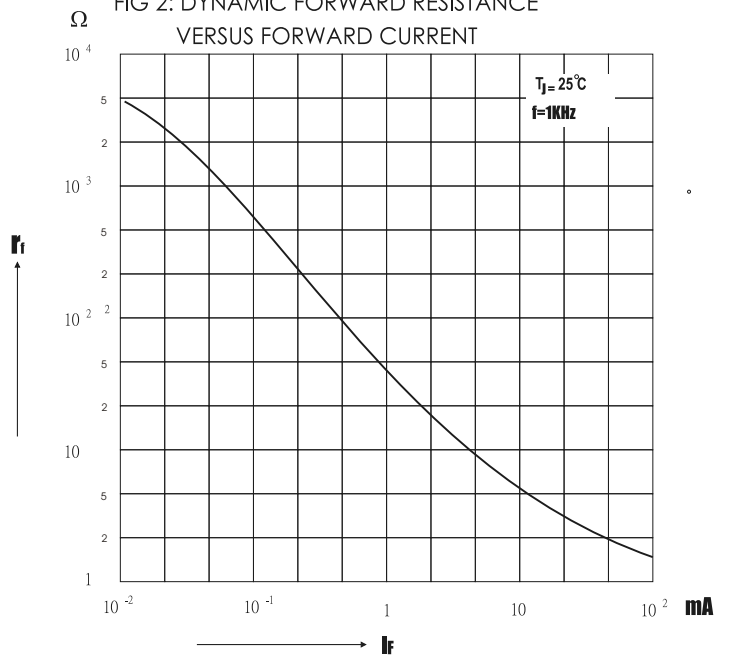


FIG 3-ADMISSIBLE POWER DISSIPATION VERSUS AMBIENT TEMPERATURE

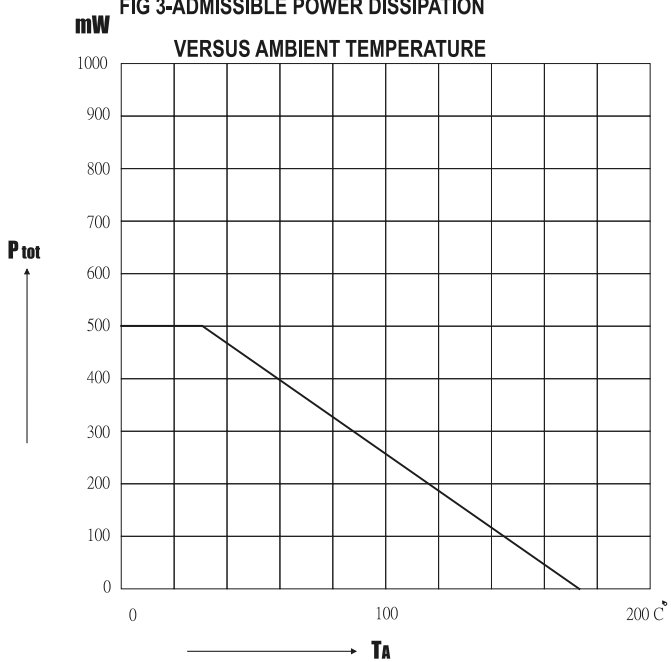


FIG. 4-RELATIVE CAPACITANCE VERSUS REVERS VOLTAGE

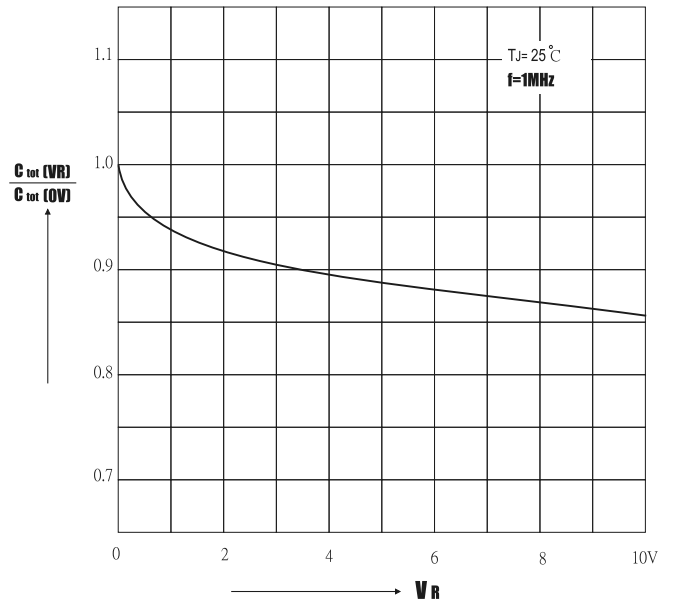


FIG.5 RECTIFICATION EFFICIENCY MEASUREMENT CIRCUIT

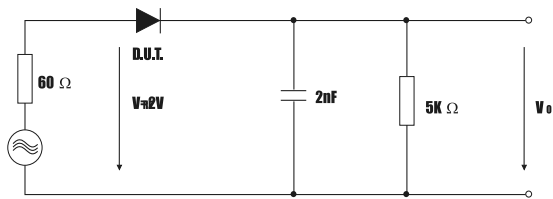


FIG 6: LEAKAGE CURRENT VERSUS JUNCTION TEMPERATURE

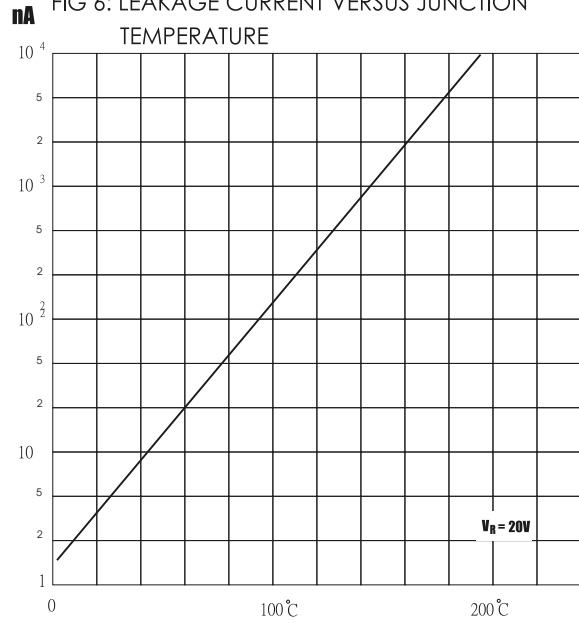


FIG 7: ADMISSIBLE REPETITIVE PEAK FORWARD CURRENT VERSUS PULSE DURATION

